

Shih-Chang Shei

List of Publications by Year in descending order

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28
papers

163
citations

1163117

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h-index

1125743

13
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28
all docs

28
docs citations

28
times ranked

241
citing authors

#	ARTICLE	IF	CITATIONS
1	White-Light Emission From GaN-Based TJ LEDs Coated With Red Phosphor. IEEE Electron Device Letters, 2016, 37, 1150-1153.	3.9	11
2	White LEDs with InP-ZnS quantum dots. , 2016, , .		0
3	Fabrication and sulfurization of Cu ₂ SnS ₃ thin films with tuning the concentration of Cu-Sn-S precursor ink. Applied Surface Science, 2016, 388, 71-76.	6.1	13
4	White LEDs with CIS-ZnS quantum dots. , 2016, , .		1
5	Thermodynamics and kinetics insight into reaction mechanism of Cu ₂ ZnSnSe ₄ nanoink based on binary metal-amine complexes in polyetheramine-synthesized process. Journal of Alloys and Compounds, 2016, 676, 54-63.	5.5	5
6	GaN-based LEDs with flower shape ZnO nanorods by SILAR-based and hydrothermal methods. , 2015, , .		0
7	GaN-Based White LEDs With CIS/ZnS Quantum Dots Synthesized Using Polyetheramine as Solvent. IEEE Journal of Quantum Electronics, 2015, 51, 1-6.	1.9	1
8	Selenization of Cu ₂ ZnSnSe ₄ thin films by rapid thermal processing. , 2015, , .		0
9	Synthesis and selenization of Cu ₂ SnSe ₃ nanocrystals by a novel solution method. , 2015, , .		0
10	Design and Fabrication of a TiO ₂ /SiO ₂ Dielectric Broadband and Wide-Angle Reflector and Its Application to GaN-Based Blue LEDs. IEEE Journal of Quantum Electronics, 2015, 51, 1-5.	1.9	6
11	Synthesis of CuInS ₂ quantum dots using polyetheramine as solvent. Nanoscale Research Letters, 2015, 10, 122.	5.7	16
12	GaN-Based Power Flip-Chip LEDs With SILAR and Hydrothermal ZnO Nanorods. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 431-435.	2.9	3
13	Synthesis of CuInS ₂ -ZnS quantum dots for different Cu/In ratios by one-pot method and its applications to white light-emitting diodes. , 2015, , .		0
14	AlGaInP-based LEDs with ZnO nanostructures by successive ionic layer adsorption and reaction and hydrothermal methods. , 2015, , .		0
15	Effect of Solvent Chelating on Crystal Growth Mechanism of CZTSe Nanoink in Polyetheramine. IEEE Nanotechnology Magazine, 2015, 14, 896-903.	2.0	1
16	Study of temperature- and time-resolved luminescence of CuInS ₂ -ZnS quantum dots synthesized by one-pot method. , 2015, , .		0
17	Multiple Nanostructures on Full Surface of GZO/GaN-Based LED to Enhance Light-Extraction Efficiency Using a Solution-Based Method. IEEE Journal of Quantum Electronics, 2014, 50, 629-632.	1.9	47
18	Synthesis of CZTSe Nanocrystal Prepared by a Facile Route in Coordinating Solvent From Elemental Sources. IEEE Nanotechnology Magazine, 2013, 12, 532-538.	2.0	4

#	ARTICLE	IF	CITATIONS
19	SiN Nanopillars on GaN-Based LED to Enhance Light-Extraction Efficiency by a Successive Ionic Layer Adsorption and Reaction Method. Journal of Lightwave Technology, 2013, 31, 2413-2418.	4.6	2
20	Optical and Structural Properties of Titanium Dioxide Films from and Starting Materials Annealed at Various Temperatures. Advances in Materials Science and Engineering, 2013, 2013, 1-7.	1.8	15
21	AlGaInP-Based LEDs With AuBe-Diffused AZO/GaP Current Spreading Layer. IEEE Journal of Quantum Electronics, 2013, 49, 846-851.	1.9	9
22	Highly Transparent Nano-Needle ZnO Prepared by Successive Ionic Layer Adsorption and Reaction Method. Integrated Ferroelectrics, 2013, 143, 87-96.	0.7	0
23	GaN-Based LEDs With Contact-Transferred and Mask-Embedded Lithography and In-Situ N_2 Treatments. Journal of Lightwave Technology, 2012, 30, 3241-3246.	4.6	1
24	GaN-Based LEDs with a Mirror Structure and an Insulating Layer. , 2012, , .		0
25	GaN-Based LEDs With Omnidirectional Metal Underneath an Insulating SiO_2 Layer. IEEE Photonics Technology Letters, 2012, 24, 815-817.	2.5	8
26	Back Cover: Investigation of Ni/Ag contact to GaN with an O_2 plasma treatment and its application to GaN-based LEDs (Phys. Status Solidi A 8/2012). Physica Status Solidi (A) Applications and Materials Science, 2012, 209, .	1.8	0
27	Investigation of Ni/Ag contact to GaN with an O_2 plasma treatment and its application to GaN-based LEDs. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1568-1574.	1.8	1
28	Nitride-Based LEDs With High-Reflectance and Wide-Angle Ag Mirror $\text{SiO}_2/\text{TiO}_2$ DBR Backside Reflector. Journal of Lightwave Technology, 2011, 29, 1033-1038.	4.6	19